Abstracts

Highly Consistent FET Model Parameter Extraction Based on Broadband S-Parameter Measurements

G. Kompa and M. Novotny. "Highly Consistent FET Model Parameter Extraction Based on Broadband S-Parameter Measurements." 1992 MTT-S International Microwave Symposium Digest 92.1 (1992 Vol. I [MWSYM]): 293-296.

A new FET model parameter extraction procedure is proposed which yields highly consistent model element values of a widely used 15-element model. For unique extraction of the elements from hot scattering parameters, the gate resistance R/sub g/ is previously derived from cold S-parameter coefficients measured at gate-voltages lower then the pinch-off voltage.

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